In the Claims:

Please amend the claims as follows. A complete listing of the claims proper claim identifiers is set forth below.

1.   (Currently Amended) A method of processing a workpiece ~~(52)~~, the method comprising the steps of:

~~in which a workpiece (52) to be processed~~ fastening a workpiece (52) to be processed ~~is fastened~~ to a work carrier ~~(10)~~ by means of a solid ~~(62)~~,

wherein the work carrier ~~(10) containing a porous material or being made of~~ comprises a porous material.

2.   (Currently Amended) The method as claimed in claim 1, wherein the work carrier comprises a gas-permeable work carrier ~~(10) is used, and wherein a vacuum (64) is generated at the work carrier (10) for the fastening, preferably after the application of the solid (62) in liquefied form and/or before the hardening of the solid (62)~~.

3.   (Currently Amended) The method as claimed in claim 1 or 2, wherein the solid ~~(62)~~ for separating the workpiece ~~(52)~~ and work carrier ~~(10)~~ is released by means of a solvent ~~(90), the solvent (90) penetrating into pores (14 to 20) of the work carrier (10)~~.

4.   (Currently Amended) The method as claimed in claim 3, wherein a work carrier ~~(10)~~ which is permeable to said solvent ~~(90)~~ is used~~, and wherein, to separate the workpiece (52) and work carrier (10), solvent penetrates into passages (24, 26) from a pore or from a plurality of pores (14 to 20) through the work carrier (10) up to the solid (62), preferably by capillary action or by the generation of a positive pressure (104) or of a vacuum (102), in particular on a side of the work carrier (10) which is remote from the workpiece (52)~~.

5.   (Currently Amended) The method as claimed in claim 1 ~~one of the preceding claims~~, wherein the porous material is a ceramic, a glass, a glass ceramic, a metal, in particular a sintered metal, a metal ceramic or a sintered material~~, and/or wherein the average pore size has a value of between 20 μm and 500 μm or between 50 μm and 100 μm, and/or wherein the porosity of the porous material has a value of between 20% and 50%, and/or wherein the value of the open porosity of the porous material lies between 10% and 60% or between 20% and 50%, and/or~~

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~~wherein at least 10% or at least 20% of the pore volume belongs to pore passages (24, 26)~~ ~~passing through the porous material, and/or wherein the porous material used is P65 or P55,~~ ~~and/or wherein the pores (14 to 22) are arranged irregularly and/or according to a uniform~~ ~~distribution.~~

6.   (Currently Amended) The method as claimed in one of the preceding claims, wherein the workpiece ~~(52)~~ is thinned on the work carrier ~~(10), in particular to a thickness less~~ ~~than 100 μm or less than 20 μm, preferably ground and/or polished and/or etched, in particular in~~ ~~a wet-chemical, chemical or chemical/physical manner, and/or the workpiece (52) on the work~~ ~~carrier (10) is subjected to a lithographic process, in particular irradiation, and/or the workpiece~~ ~~(52) on the work carrier (10) is subjected to a layer-deposition process.~~

7.   (Currently Amended) The method as claimed in <u>claim 1</u> ~~one of the preceding~~ ~~claims,~~ wherein the solid ~~(62)~~ <u>comprises a material from a group consisting of: wax, adhesive, a</u> <u>plastic material, or a double-sided adhesive tape.</u> ~~contains wax or adhesive or a plastic material~~ ~~or a double-sided adhesive tape or is made of one of these materials.~~

8.   (Currently Amended) The method as claimed in <u>claim 1</u> ~~one of the preceding~~ ~~claims,~~ wherein the workpiece ~~(52)~~ contains a semiconductor material~~, in particular silicon, or is~~ ~~made of a semiconductor material, and/or wherein the workpiece (52) is a semiconductor wafer~~.

9.   (Currently Amended) The method as claimed in <u>claim 1</u> ~~one of the preceding~~ ~~claims,~~ wherein the solid ~~(62)~~ fills <u>at least a portion of an</u> ~~the entire~~ intermediate space between workpiece ~~(52)~~ and work carrier ~~(10), or the solid (62) fills only part of the intermediate space~~ ~~between workpiece (52) and work carrier (10), in particular a plurality of regions separated from~~ ~~one another by intermediate spaces or an annular region which surrounds a region which is not~~ ~~filled~~.

10.   (Currently Amended) A work carrier <u>for processing a workpiece, said work</u> <u>carrier comprising</u> ~~(10), in particular a work carrier (10) used in a method as claimed in one of the~~ ~~preceding claims, having the shape of a plate or a disk, wherein the work carrier (10) contains~~ a porous material ~~or is made of a porous material~~.

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11.　(Currently Amended)　The work carrier ~~(10)~~ as claimed in claim 10, wherein the ~~work carrier (10) has the outline of a semiconductor wafer (52), and wherein the~~ diameter (DM1) of the work carrier ~~(10)~~ is equal to the diameter of the semiconductor wafer ~~(25)~~.

12.　(New)　The method as claimed in claim 1 wherein a vacuum is generated at the work carrier for the fastening.

13.　(New)　The method as claimed in claim 12 wherein the vacuum is generated after the application of the solid in liquefied form and before the hardening of the solid.

14.　(New)　The method of claim 4 wherein, to separate the workpiece and work carrier, said solvent penetrates into passages from a pore or from a plurality of pores through the work carrier up to the solid.

15.　(New)　The method of claim 14 wherein the reparations of the workpiece from the work carrier preferably comprises reparation by the generation of a positive pressure on a side of the work carrier which is remote from the workpiece.

16.　(New)　The method as claimed in claim 1, wherein the average pore size has a value of between 20μm and 500μm or between 50μm and 100μm, and/or wherein the porosity of the porous material has a value of between 20% and 50%.

17.　(New)　The method as claimed in claim 1, wherein the value of the open porosity of the porous material lies between 10% and 600 or between 20% and 50%.

18.　(New)　The method as claimed in claim 1, wherein at least 10% or at least 20% of the pore volume belongs to pore passages (24, 26) passing through the porous material.

19.　(New)　The method as claimed in claim 1, wherein the porous material used is P65 or P55, and/or wherein the pores (14 to 22) are arranged irregularly and/or according to a uniform distribution.

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